In The Claims:

1. (Currently Amended) A method for depositing a material [[(3)]] on a substrate wafer [[(1)]] having the following method steps:

(a) providing the substrate wafer [[(1)]], which has a growth area [[(4)]] intended for a later material deposition;

(b) applying a thermal radiation absorption layer [[(2)]], which exhibits a good absorption of thermal radiation, on a rear side [[(5)]] of the substrate wafer [[(1)]] which faces away from the growth area [[(4)]];

(c) heating the substrate wafer [[(1)]] to a deposition temperature;

(d) depositing a material [[(3)]] onto the growth area [[(4)]] of the substrate wafer [[(1)]] by an MOVPE method;

wherein the substrate wafer is heated by the thermal radiation absorption layer during MOVPE ~~is applied before deposition of the material onto the growth area of the substrate wafer~~.

2. (Currently Amended) The method according to Claim 1, in which the deposited material [[(3)]] is a semiconductor material.

3. (Currently Amended) The method according to Claim 1,in which the deposited material [[(3)]] comprises at least one layer made of $Al_xGa_yIn_{1-x-y}N$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$ apply.

4. (Previously Presented) The method according to claim 1, in which a substrate wafer is used which essentially comprises SiC or an SiC-based material.

5. (Currently Amended) The method according to claim 1, in which a material or a material mixture which exhibits inert behaviour during the deposition method in accordance with method step (d) is applied as the thermal radiation absorption layer [[(2)]].

6. (Currently Amended) The method according to claim 1, in which a material or a material mixture which is compatible with a material and/or a contact-connecting process of an electrical contact that is to be applied later, is applied as the thermal radiation absorption layer [[(2)]].

7. (Currently Amended) The method according to claim 1, in which the thermal radiation absorption layer [[(2)]] is applied by means of sputtering in accordance with method step (b).

8. (Currently Amended) The method according to claim 1, in which a doped Si layer, in particular a highly doped Si layer, is used as the thermal radiation absorption layer [[(2)]].

9. (Previously Presented) The method according to Claim 8, in which the Si layer is applied with a thickness which lies between 10 nm and 20 μm inclusive.

10. (Previously Presented) The method according to Claim 8, in which the Si layer has a doping of at least $1 \times 10^{19}/cm^3$.

11. (Previously Presented) The method according to claim 1, in which the heating in accordance with method step (c) is essentially effected by means of thermal radiation.

12. (Currently Amended) The method according to claim 1, in which, in method step (c), a heating source is used which generates thermal radiation of a spectral range for which the thermal radiation absorption layer [[(2)]] exhibits good radiation absorption.

13. (New) The method according to claim 1, in which a non-metallic layer is used as the thermal radiation absorption layer.